

3. (New) A method for filling contact holes with metal by 2-step deposition of selective tungsten layers, comprising the steps of:

providing a silicon substrate;

forming a field oxide layer and a junction layer and gate electrode on said silicon substrate;

form a first insulating layer on the whole structure;

forming first contact holes by removing the desired portion of the first insulating layer to expose said junction layer and gate electrode;

filling first metal layers into the first contact holes, entirely;

forming a conductive layer pattern on the first insulating layer spaced from said first metal layers;

forming a second insulating layer on the whole structure;

forming a second contact hole by removing the desired portion of said second insulating layer to expose both the first metal layer in said first contact hole and a conductive layer spaced from said first contact hole;

filling a second metal layer into said second contact hole to contact with the first metal layer and the conductive layer;

wherein the first metal layer and second metal layer are both formed by chemical vapor deposition method.